JMTK1404A

Features

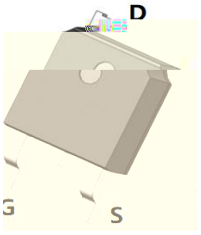
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% Vds Tested
- Halogen-free; RoHS-compliant

Applications

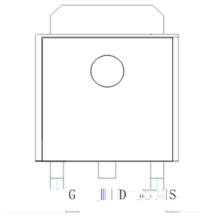
- Load Switch
- PWM Application
- Power Management

Product Summary

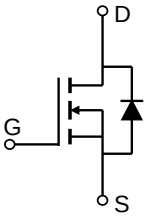
Parameters	Value	Unit
V_{DSS}	40	V
$V_{GS(th)_Typ}$	2.7	V
I_D(@V_{GS}=10V)	79	A
$R_{DS(ON)_Typ}$(@V_{GS}=10V)	3.1	m :



TO-252-3L Top View



Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMTK1404A	JMTK1404A	3	Tape&Reel	TO-252-3L	2500	25000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		40	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	79	A
		T_C = 100°C	50	
I_{DM}	Pulsed Drain Current [1]		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy [2]		306	mJ
P_D	Power Dissipation	T_C = 25°C	50	W
		T_C = 100°C	20	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
R	Thermal Resistance, Junction to Ambient[3]	39	°C/W
R	Thermal Resistance, Junction to Case	2.5	

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Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250 PA, V_{GS} = 0V	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 40V, V_{GS} = 0V	-	-	1.0	PA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 PA	1.9	2.7	3.8	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 30A	-	3.1	4.4	m :
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	1.6	-	:
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 20V, f = 1MHz	3475	4865	6567	pF
C_{oss}	Output Capacitance		370	518	700	pF
C_{rss}	Reverse Transfer Capacitance		220	309	417	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 20V, I_D = 20A	54	75	102	nC
Q_{gs}	Gate Source Charge		18	25	34	nC
Q_{gd}	Gate Drain("Miller") Charge		11	16	22	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 20V I_D= 20A, R_{GEN} = 3 :	-	18	-	ns
t_r	Turn-On Rise Time		-	26	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	42	-	ns
t_f	Turn-Off Fall Time		-	13	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	79	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	318	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 30A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	20	28	38	ns
Qrr	Body Diode Reverse Recovery Charge		-	22.6	-	nC

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.

2. E_{AS} condition: Starting T_J=25C, V_{DD}=20V, V_{GS}=10V, R_G=25ohm, L=0.5mH, I_{AS}=35A, V_{DD}=0V during time in avalanche.

3. R is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.

4. Pulse Test: Pulse Width 0.5%.

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Typical Performance Characteristics

Figure 1: Power De-rating

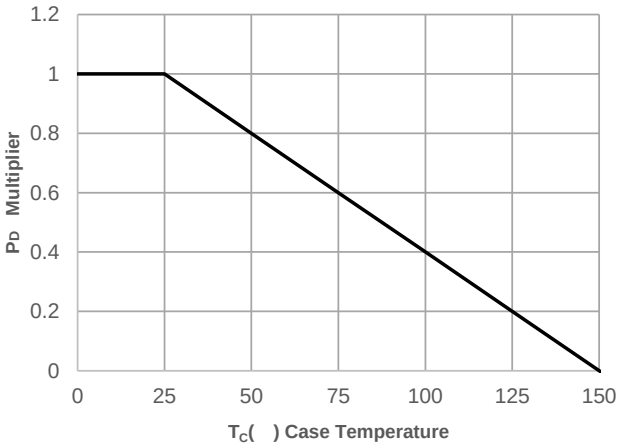
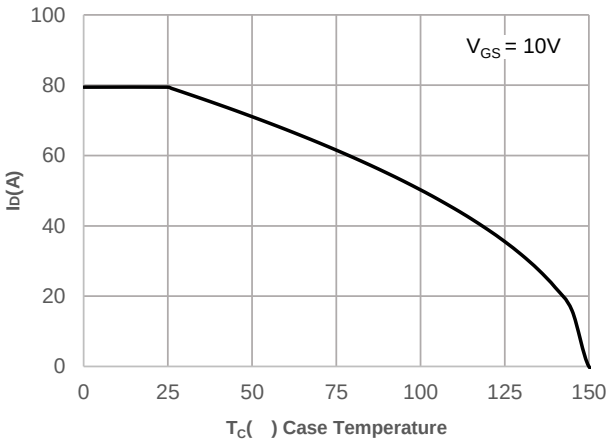
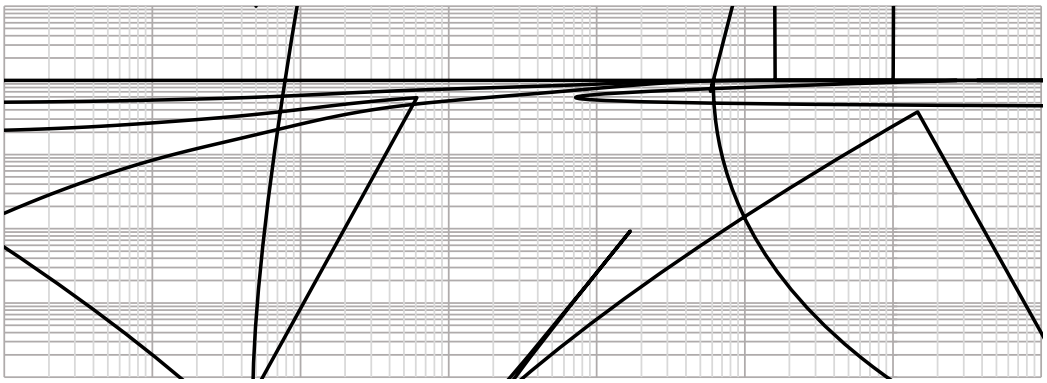


Figure 2: Current De-rating





Typical Performance Characteristics

Figure 5: Output Characteristics

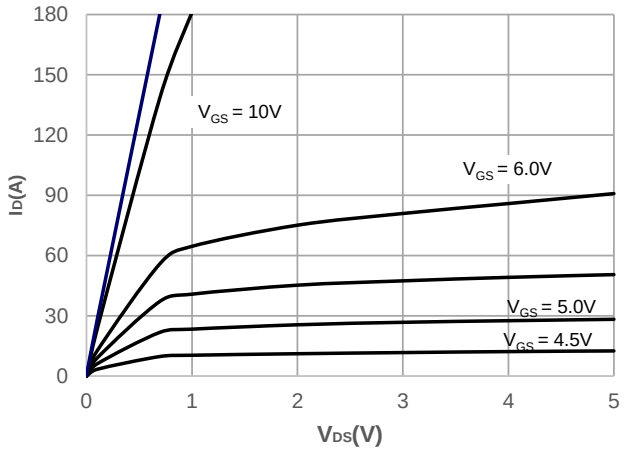


Figure 6: Typical Transfer Characteristics

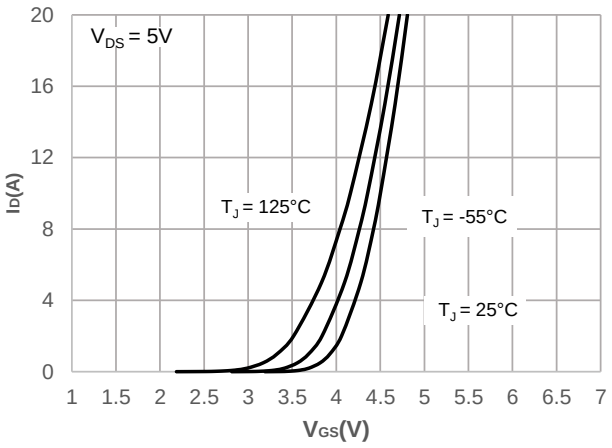


Figure 7: On-resistance vs. Drain Current

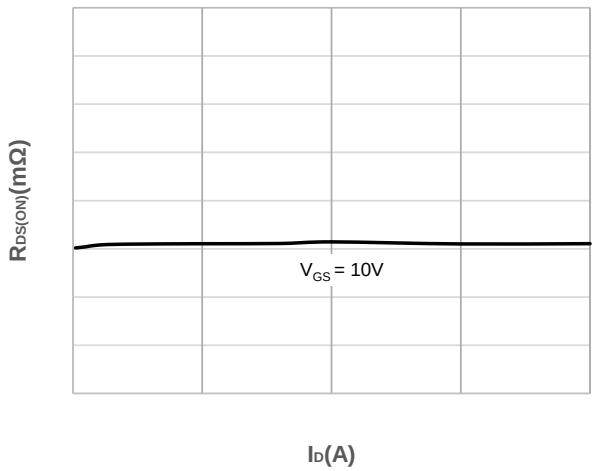
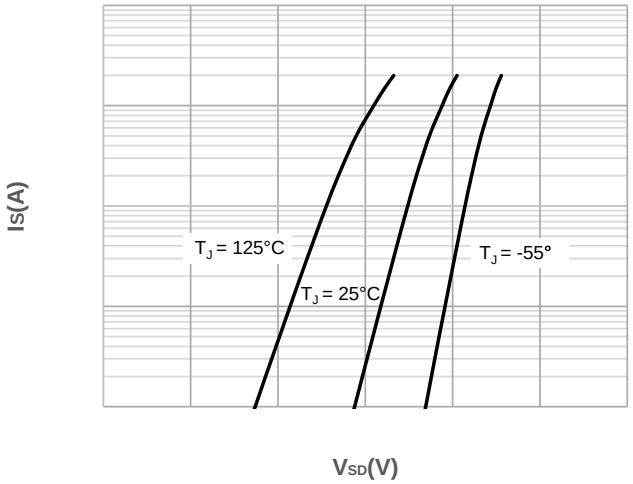


Figure 8: Body Diode Characteristics



Typical Performance Characteristics



Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

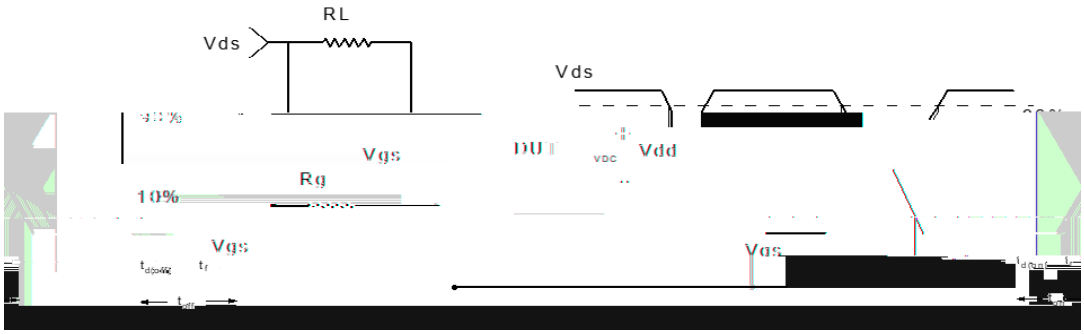


Figure 2: Resistive Switching Test Circuit & Waveform

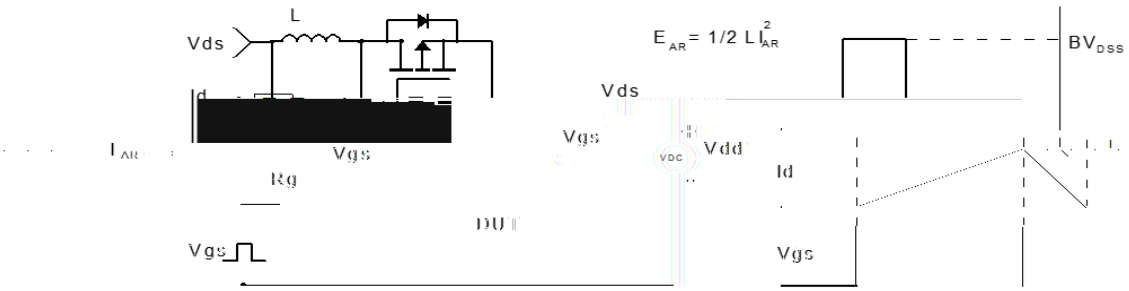


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

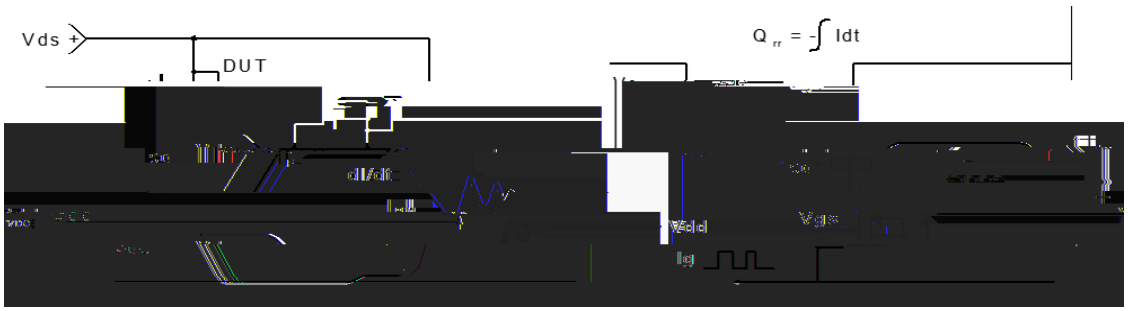
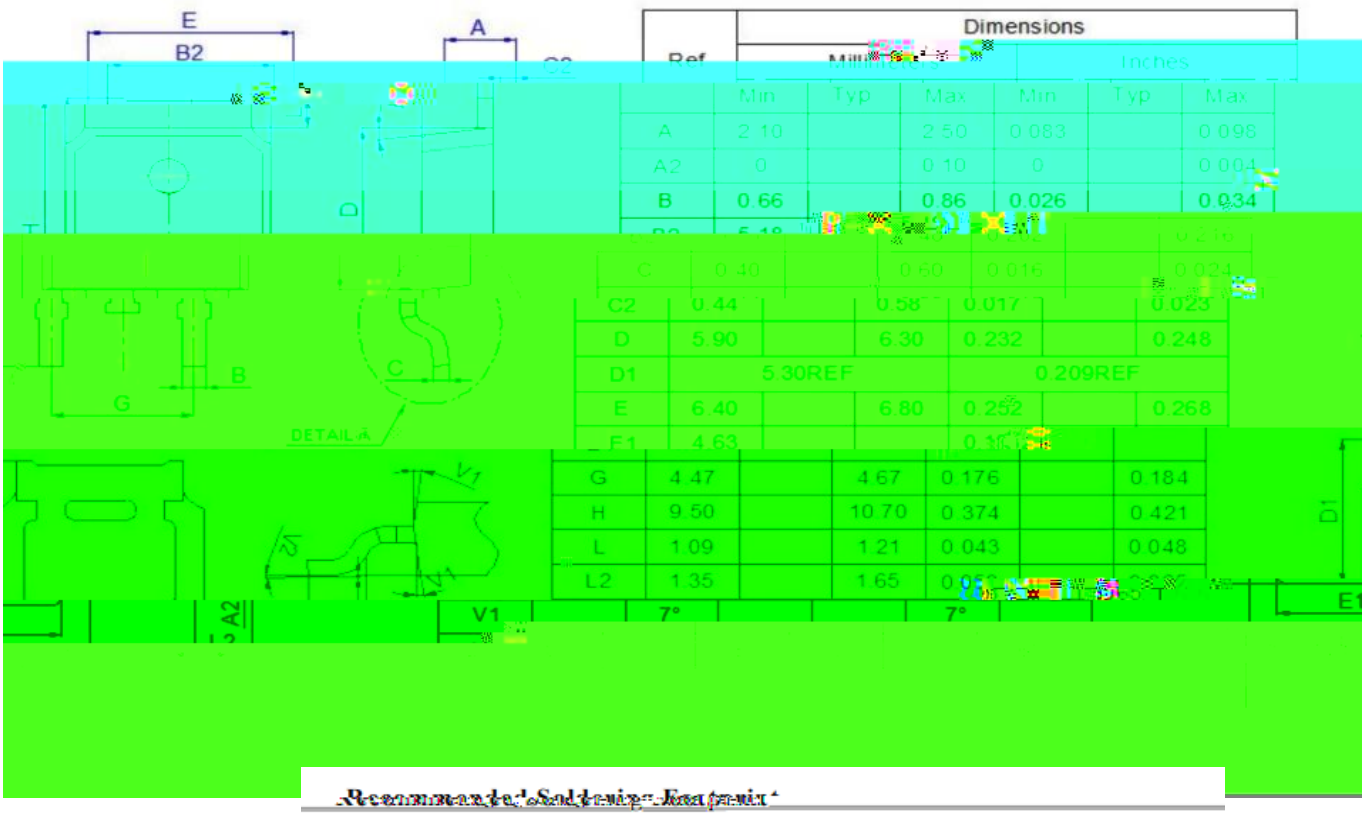


Figure 4: Diode Recovery Test Circuit & Waveform

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Package Mechanical Data(TO-252-3L)



Ref	Dimensions					
	Millimeters			Inches		
	Min	Typ	Max	Min	Typ	Max
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18					
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
T	7°		7°			



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